Abstracts

Empirical load-line capacitance models for HEMT

Y.C. Leong and S. Weinreb. "Empirical load-line capacitance models for HEMT." 2000 MTT-S International Microwave Symposium Digest 00.3 (2000 Vol. III [MWSYM]): 1385-1388.

Models for describing the gate-source and gate-drain capacitances' variation along a resistive load line have been proposed. They are charge conservative and consistent with the small-signal model at bias points along the load line. The extraction procedure for the models' parameters is fast and intuitive. The models can be implemented easily in most circuit simulator programs.

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